



A	2020.11.26	ALL	BRCS80N03DP		



/ Descriptions

DFN 3*3A-8L N MOS

N-Channel Enhancement Mode Field Effect Transistor in a DFN 3*3A-8L Plastic Package.

/ Features

$V_{DS} (V) = 30V$

$I_D = 40 A (V_{GS} = \pm 20V)$

$R_{DS(ON)} @ 10V \leq 6mR (Typ. 4.7mR)$

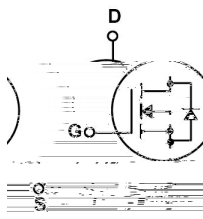
。 HF Product.

/ Applications

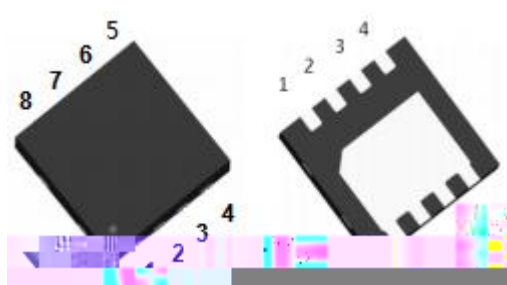
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



出脚	定义
1	Gate
2	Drain
3	Source
4	Gate
5	Drain
6	Source
7	Gate
8	Drain

/ Marking

See Marking Instructions.



Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	30	V
Drain Current		$I_D(T_C=25^{\circ}\text{C})$	40	A
Drain Current - Pulsed		I_{DM}	130	A
Gate-Source Voltage		V_{GSS}	± 20	V
Single Pulsed Avalanche Energy		E_{AS}	211	mJ
Avalanche Current		I_{AS}	23	A
Power Dissipation		$P_D(T_C=25^{\circ}\text{C})$	29	W
Operating and Storage Temperature Range		T_J, T_{stg}	-55 to 150	
Junction-to-Ambient	$t \leq 10$	$R_{\theta JA}$	40	$^{\circ}\text{C/W}$
Junction-to-Ambient	Steady-State		75	
Junction-to-Case	Steady-State	$R_{\theta JC}$	4.2	

BRCS060



() /



Note:

- | | | | | | |
|---|-------|-----|-----------|--------|--|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180°C, Time:60~90sec. |
| 2 | 245±5 | | 5±0.5sec; | | 2.Peak Temp.:245±5°C, Duration:5±0.5sec. |
| 3 | | 2 | 10°C/sec. | | 3. Cooling Speed: 2~10°C/sec. |

/ Resistance to Soldering Heat Test Conditions

260±5°C	10±1 sec.	Temp.:260±5	Time:10±1 sec
---------	-----------	-------------	---------------

/ Packaging SPEC.

/ REEL

Package Type !	Units " # \$					Dimension " % & (unit ' mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box (	Outer Box)
DFN 3*3A-8L	5,000	2	10,000	6	60,000	13" ×12	360×360×50	380×335×366